



**ECSE 323**  
**Digital System Design**

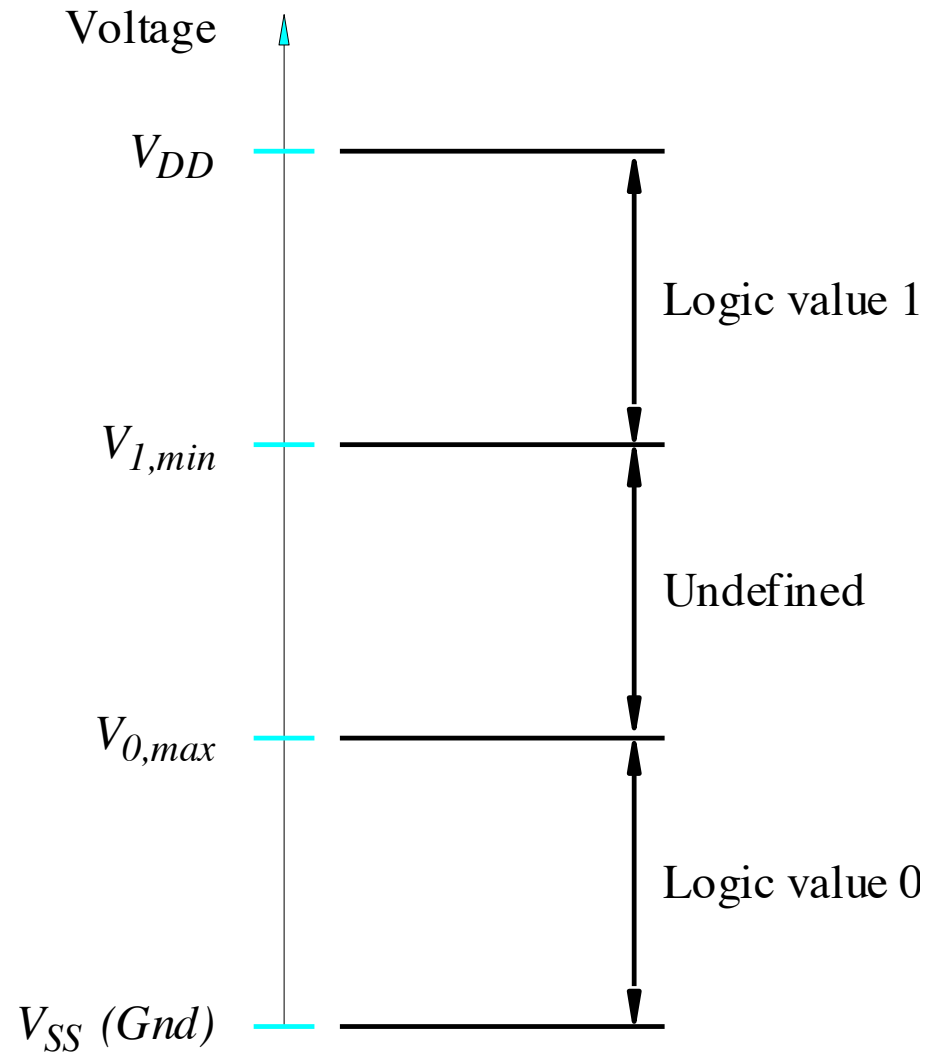
# **CMOS Digital Circuits**

**Prof. Warren Gross**

Material used in this set of slides was based on “*Fundamentals of Digital Logic with VHDL Design*”  
by S. Brown and Z. Vranesic

# Textbook Reading

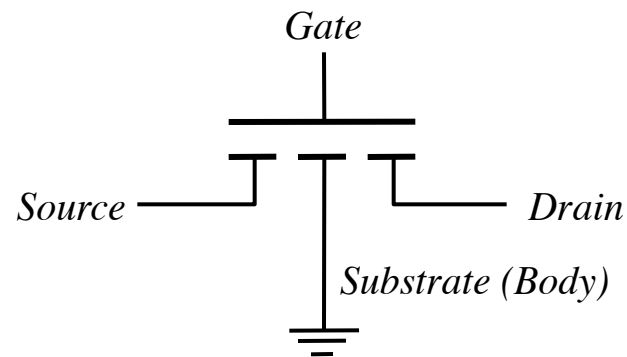
- This topic is about how logic gates are implemented using transistors.
- This topic will cover part of Chapter 3 (Implementation Technology).
- Sections 3.1-3.4, 3.8, and 3.9
- The skipped sections will be covered in a later topic



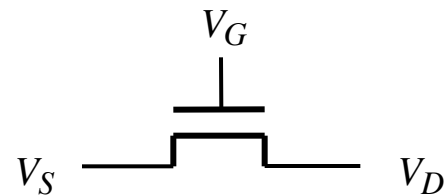
Logic values as voltage levels (positive logic system)  
Typical values of  $V_{DD} = 5V, 3.3V, 1V$



(a) A simple switch controlled by the input  $x$



(b) NMOS transistor (n-channel MOSFET)

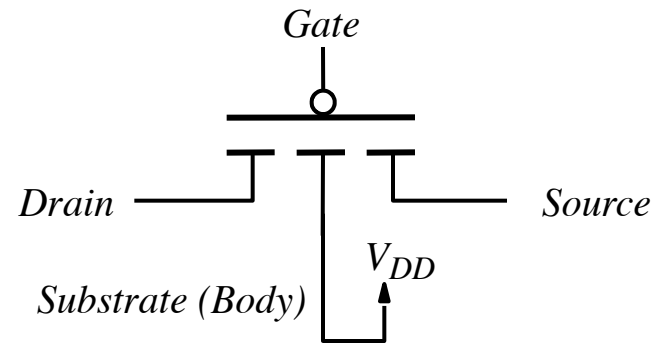


(c) Simplified symbol for an NMOS transistor.

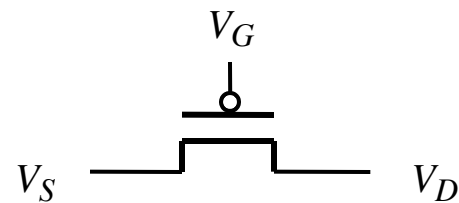
## NMOS transistor as a switch



(a) A switch with the opposite behavior of Figure 3.2 a



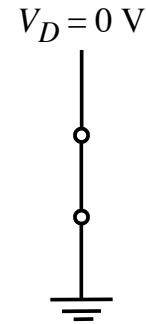
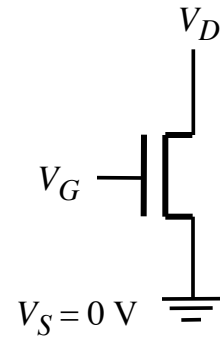
(b) PMOS transistor (p-channel MOSFET)



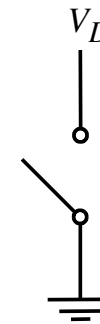
(c) Simplified symbol for a PMOS transistor

## PMOS transistor as a switch

- Convention: the terminal with the **lowest** voltage applied is the source
- $V_G$  low  $\rightarrow$  transistor is **off**
- $V_G$  high  $\rightarrow$  transistor is **on**



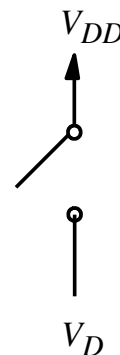
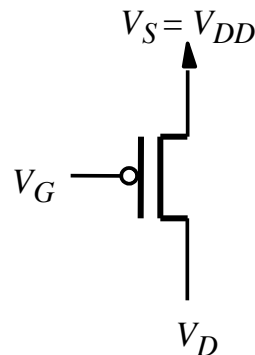
Closed switch  
when  $V_G = V_{DD}$



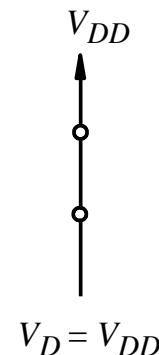
Open switch  
when  $V_G = 0$  V

(a) NMOS transistor

- Convention: the terminal with the **highest** voltage applied is the source
- $V_G$  low  $\rightarrow$  transistor is **on**
- $V_G$  high  $\rightarrow$  transistor is **off**



Open switch  
when  $V_G = V_{DD}$

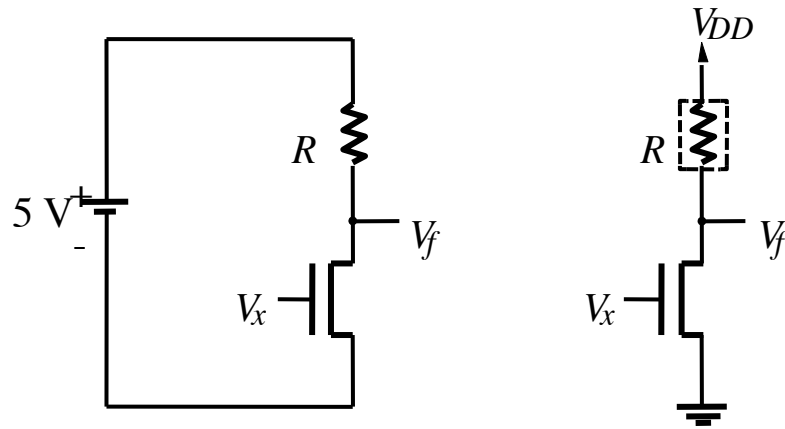


Closed switch  
when  $V_G = 0$  V

(b) PMOS transistor

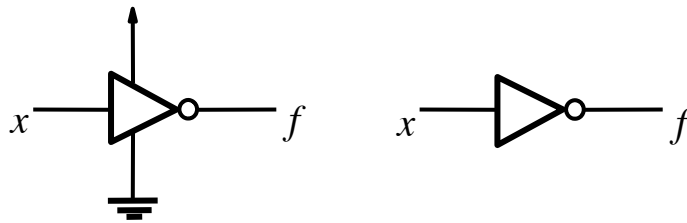
## NMOS and PMOS transistors in logic circuits

# NMOS Circuits



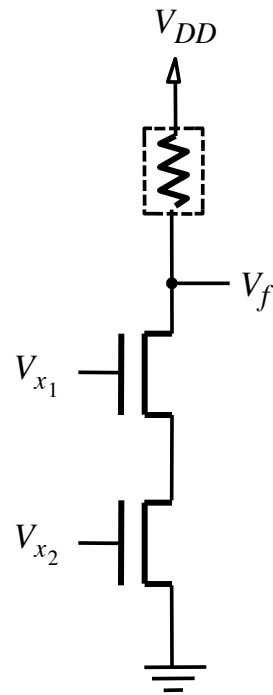
(a) Circuit diagram

(b) Simplified circuit diagram



(c) Graphical symbols

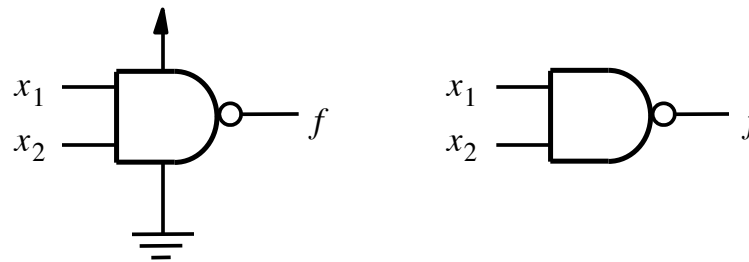
A NOT gate built using NMOS technology



(a) Circuit

$x_1$	$x_2$	$f$
0	0	1
0	1	1
1	0	1
1	1	0

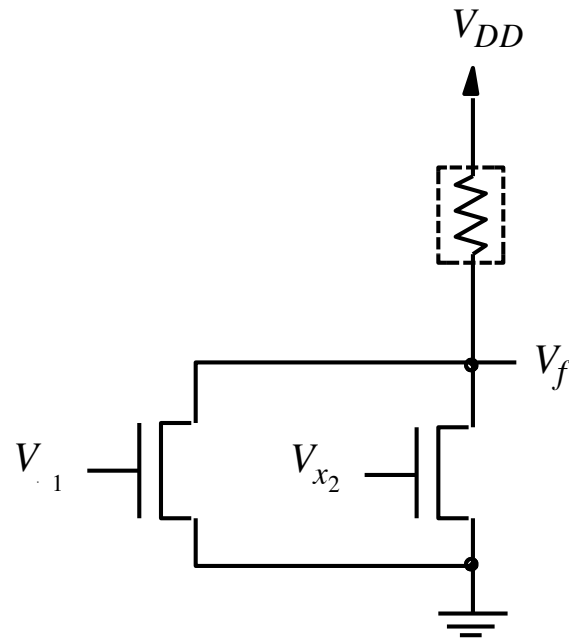
(b) Truth table



(c) Graphical symbols

NMOS realization of a NAND gate

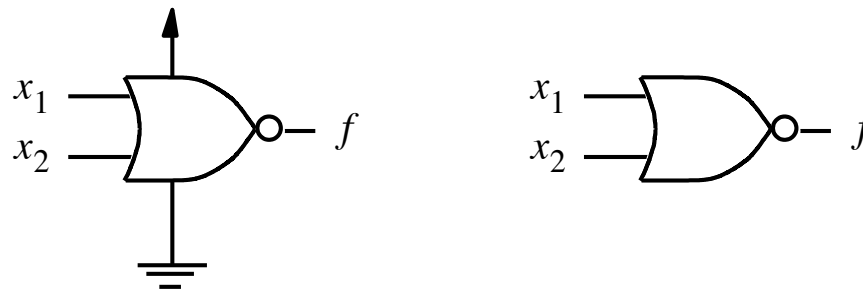




(a) Circuit

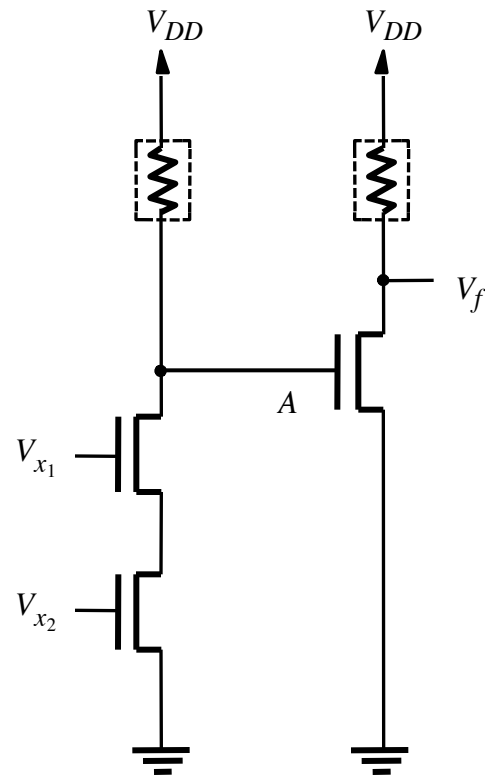
$x_1$	$x_2$	$f$
0	0	1
0	1	0
1	0	0
1	1	0

(b) Truth table



(c) Graphical symbols

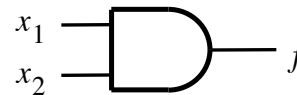
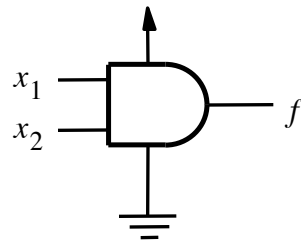
NMOS realization of a NOR gate



(a) Circuit

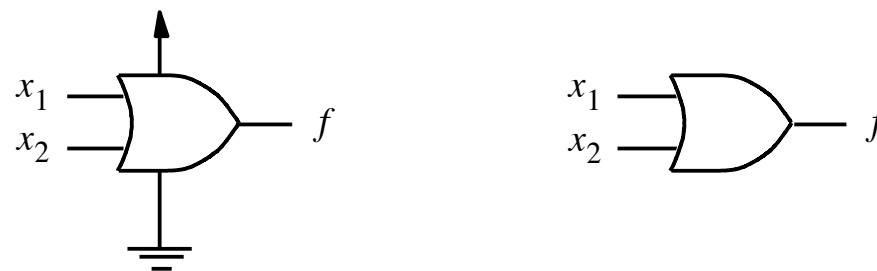
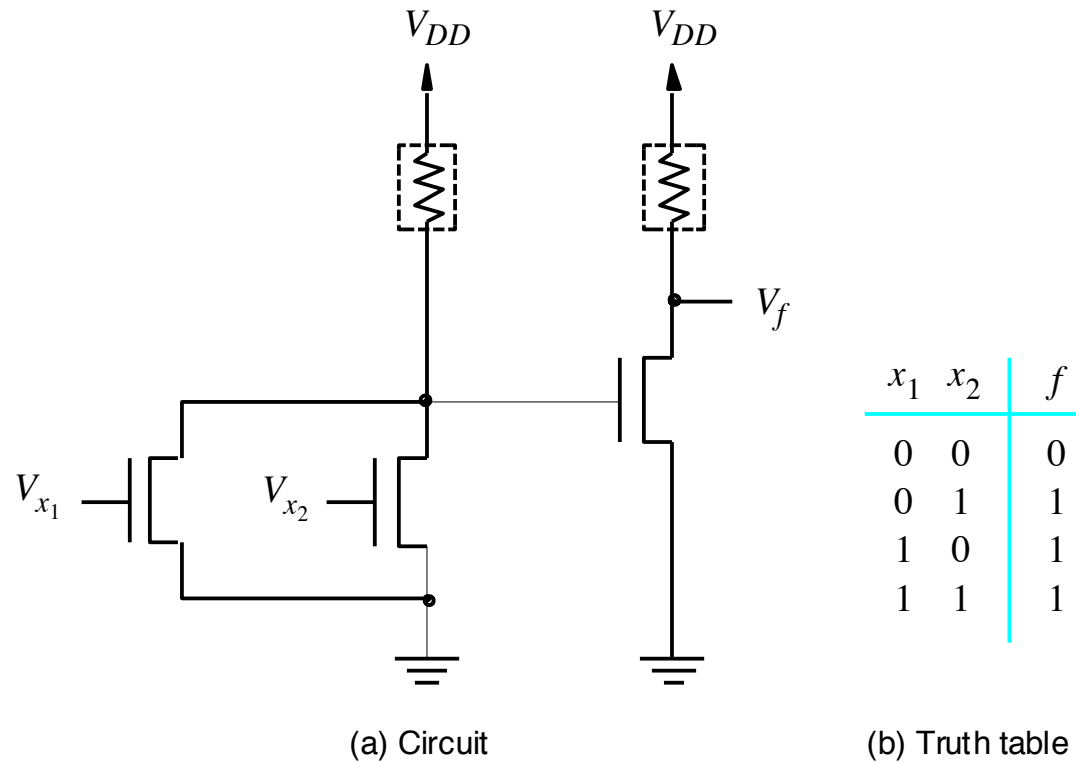
$x_1$	$x_2$	$f$
0	0	0
0	1	0
1	0	0
1	1	1

(b) Truth table



(c) Graphical symbols

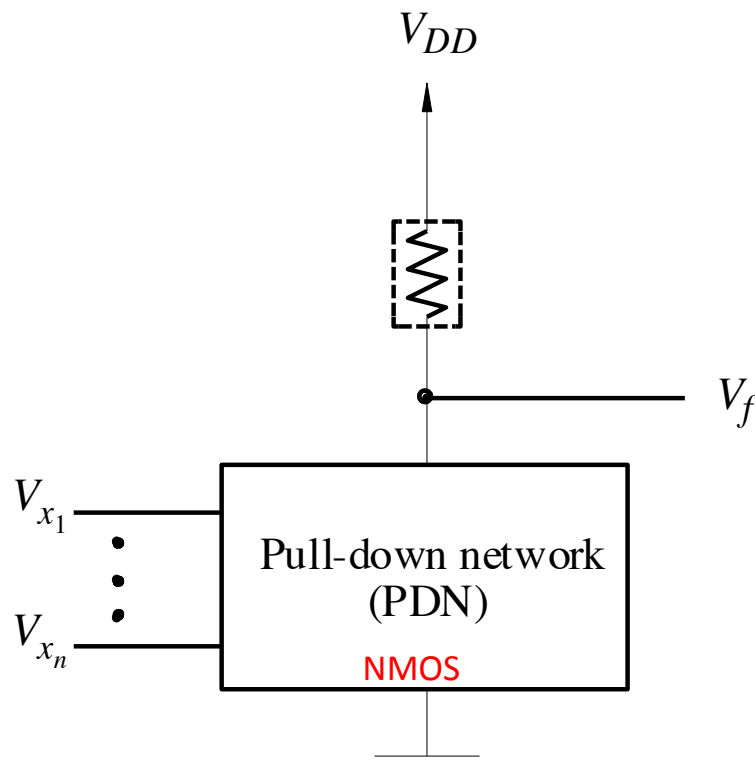
NMOS realization of an AND gate



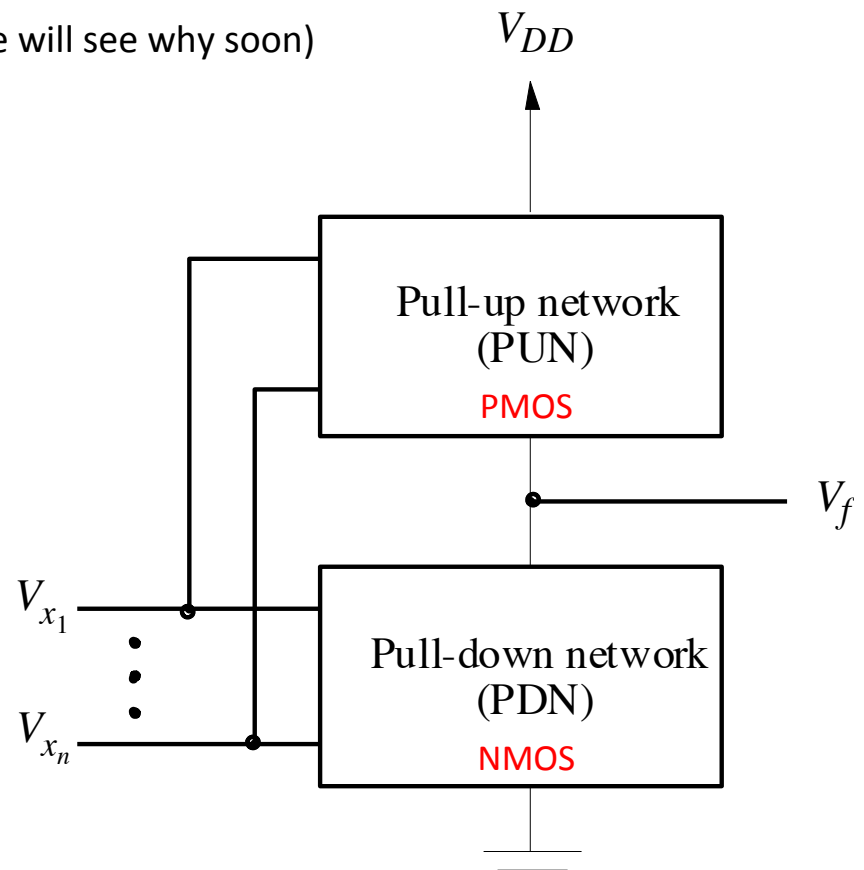
NMOS realization of an OR gate

# CMOS Circuits

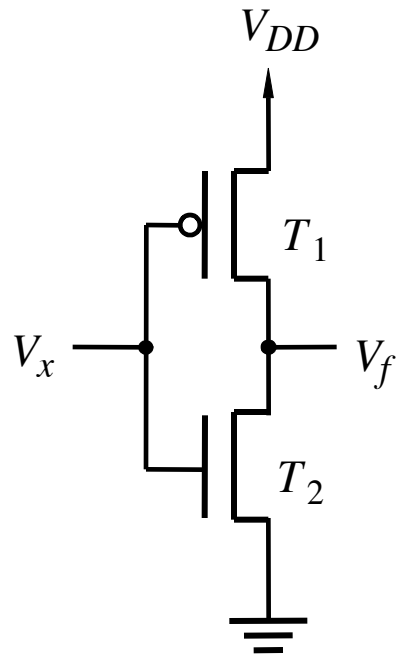
- Complementary MOS
  - uses NMOS and PMOS together
  - duals (same # transistors, series/parallel)
  - $V_f$  **either** pulled up to  $V_{DD}$  or down to Gnd
  - Why CMOS? Lower power consumption ! (we will see why soon)



NMOS gate



CMOS gate

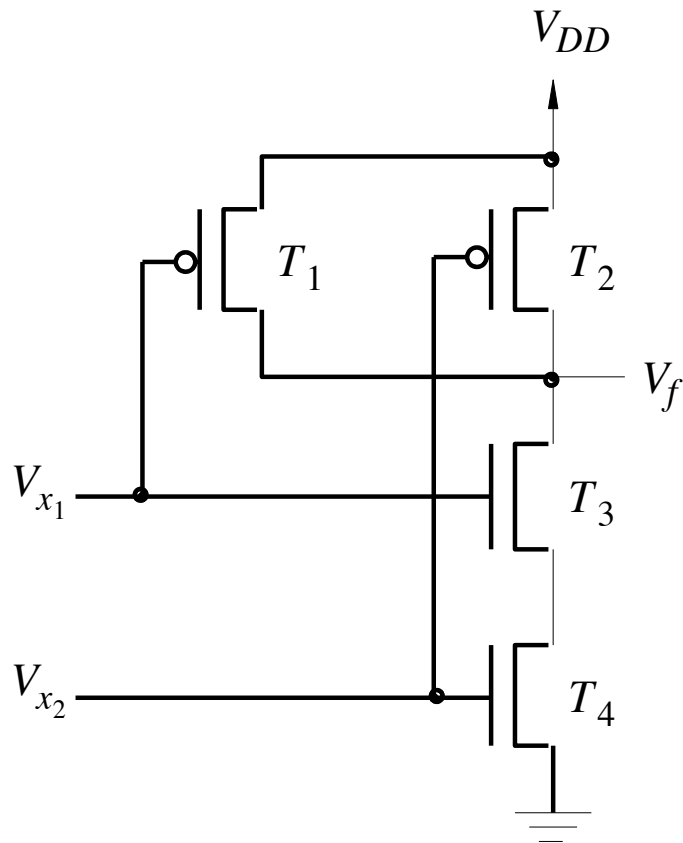


(a) Circuit

$x$	$T_1$	$T_2$	$f$
0	on	off	1
1	off	on	0

(b) Truth table and transistor states

CMOS realization of a NOT gate

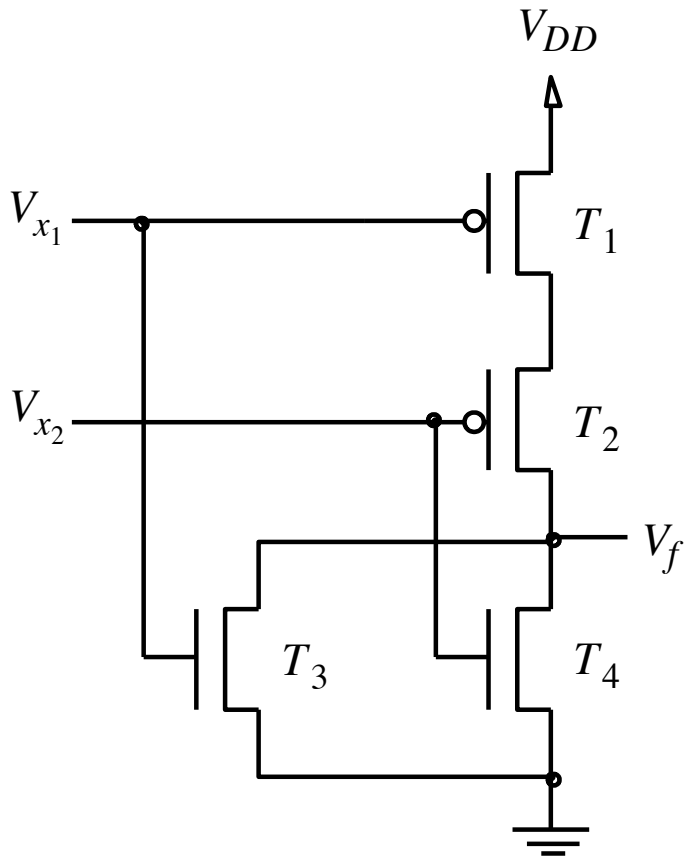


(a) Circuit

$x_1$	$x_2$	$T_1$	$T_2$	$T_3$	$T_4$	$f$
0	0	on	on	off	off	1
0	1	on	off	off	on	1
1	0	off	on	on	off	1
1	1	off	off	on	on	0

(b) Truth table and transistor states

CMOS realization of a NAND gate

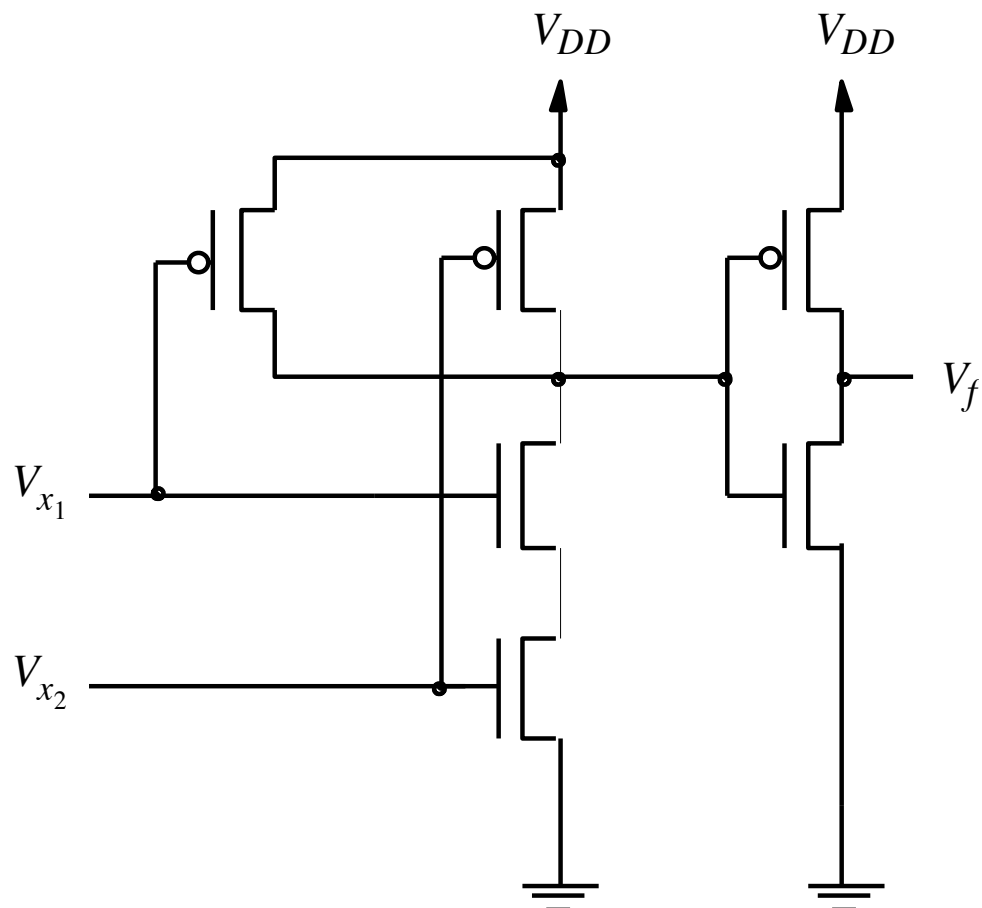


(a) Circuit

$x_1$	$x_2$	$T_1$	$T_2$	$T_3$	$T_4$	$f$
0	0	on	on	off	off	1
0	1	on	off	off	on	0
1	0	off	on	on	off	0
1	1	off	off	on	on	0

(b) Truth table and transistor states

CMOS realization of a NOR gate



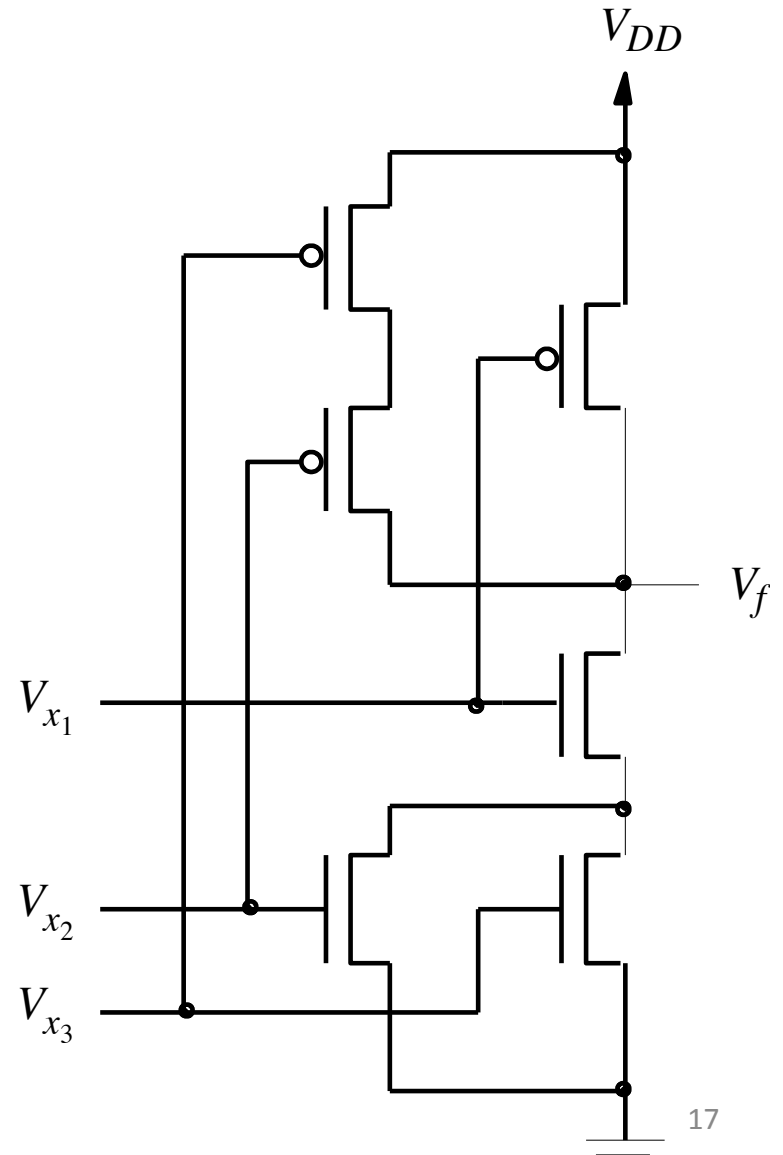
CMOS realization of an AND gate



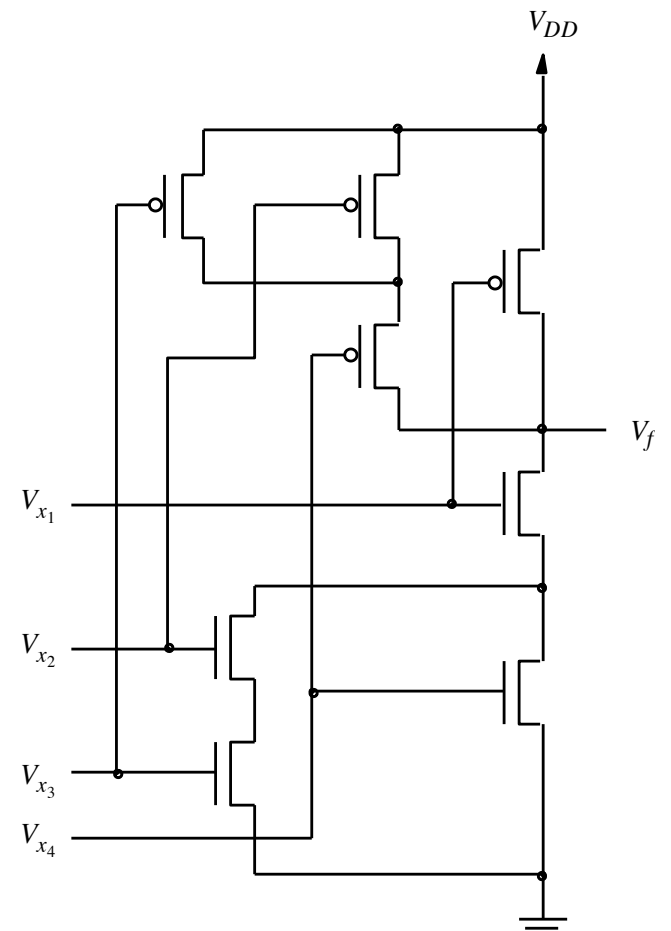
# Example 1 (Complex CMOS Gate)

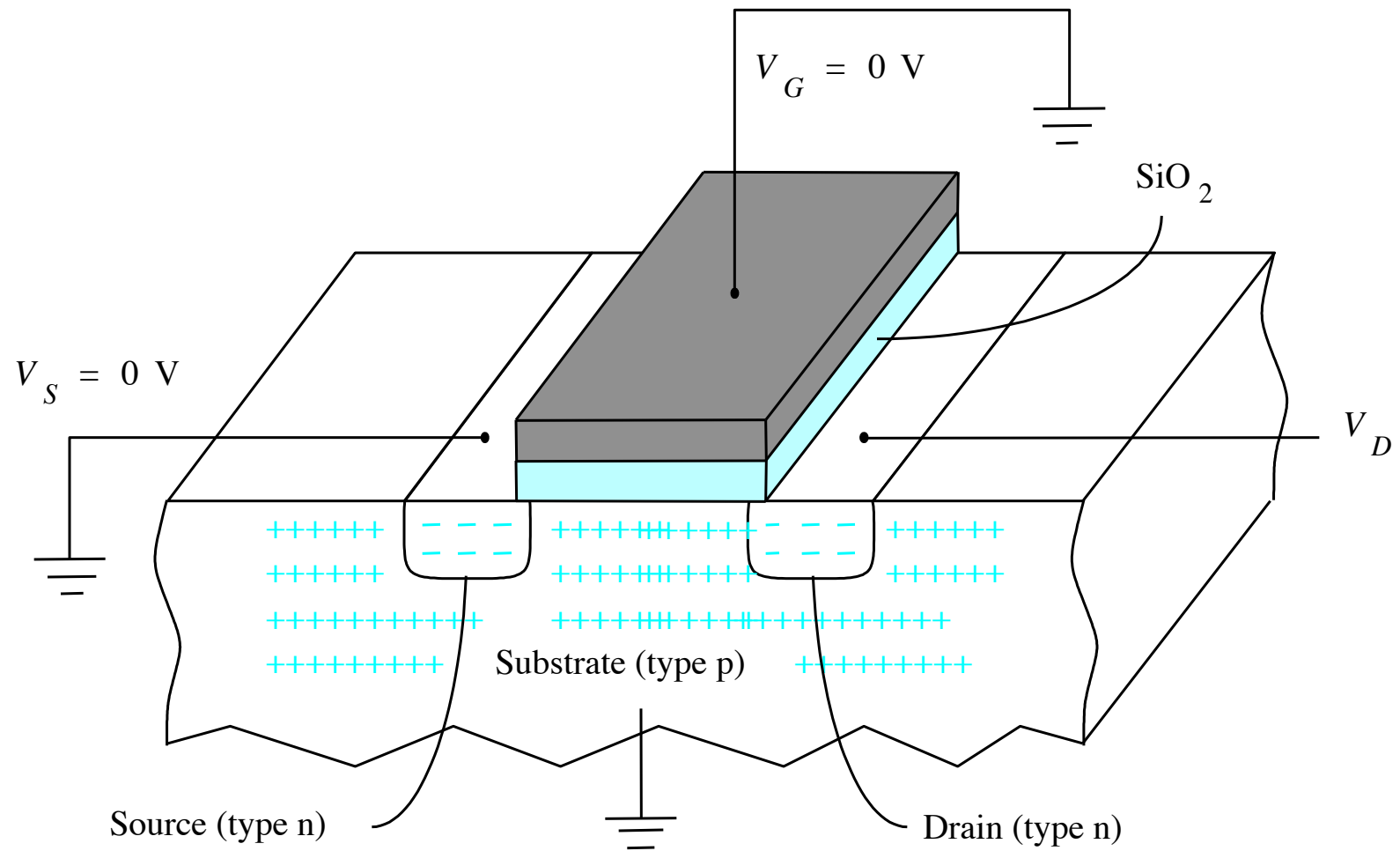
PDN: synthesize  $f'$

PUN: synthesize  $f$



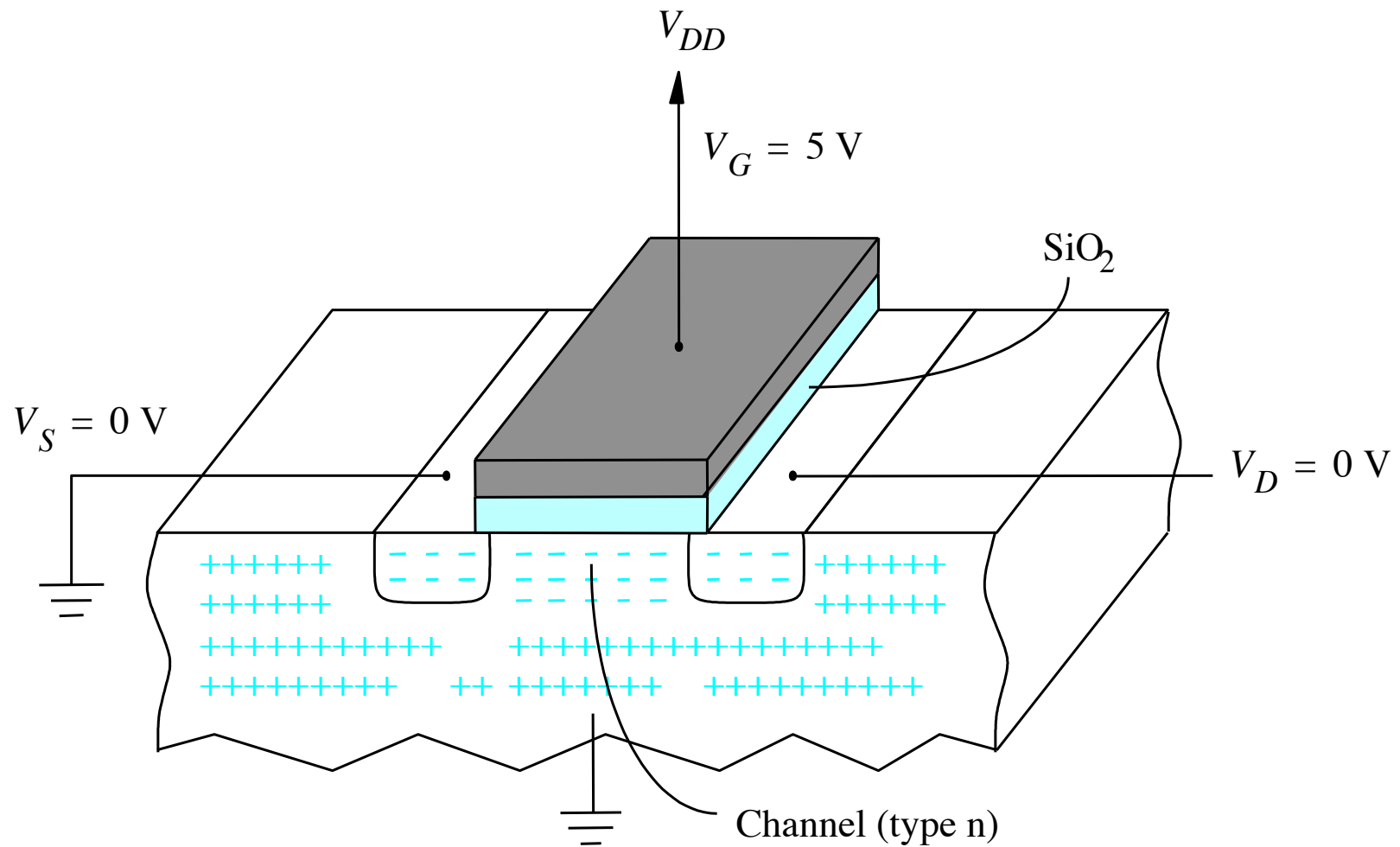
# Example 2





(a) When  $V_{GS} = 0 \text{ V}$ , the transistor is off

NMOS transistor when turned off

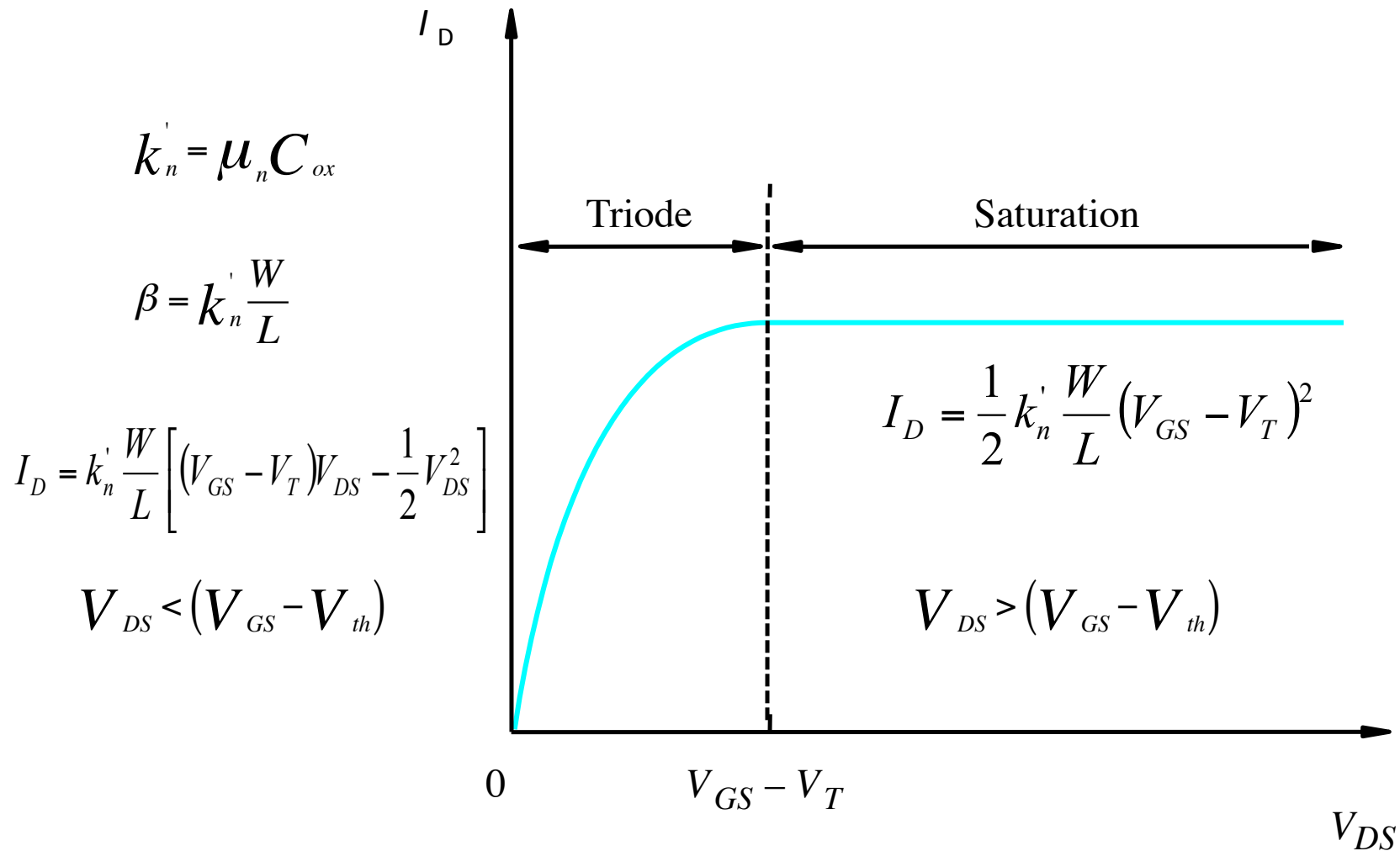


(b) When  $V_{GS} = 5\text{ V}$ , the transistor is on

NMOS transistor when turned on

$V_{GS} < V_T$  (threshold voltage)  $\rightarrow$  Transistor is off

For  $V_{GS} > V_T$ , a current,  $I_D$ , may flow from the drain to the source



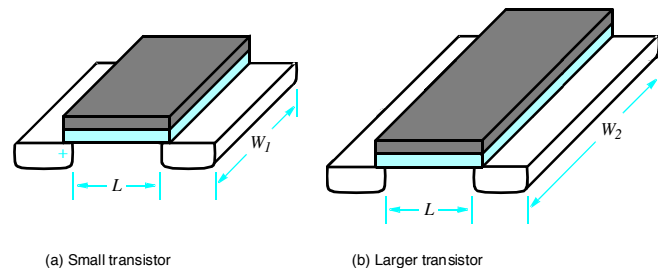
The current-voltage relationship in the NMOS transistor

# PMOS

- Same behavior as NMOS, but all voltages and currents reversed
  - Source has higher voltage,  $V_t$  is negative.
- The conduction mechanism is different in a PMOS transistor, current does not flow as readily

$$k'_p \approx 0.4k'_n$$

→ Size the W/L of the PMOS transistors 2 to 3 times larger than NMOS

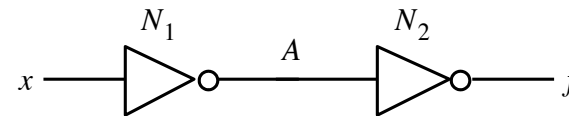


# Dynamic Operation of Logic Gates

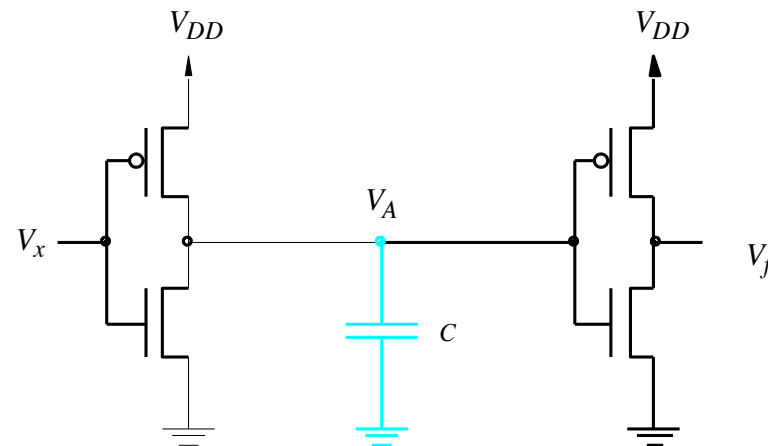
- Static – steady state
- Dynamic – when the transistor is switching

Parasitic capacitance at A caused by overlap of layers in the physical structure of the transistor (for example, the gate capacitance of  $N_2$  is seen as an output capacitance to  $N_1$ )

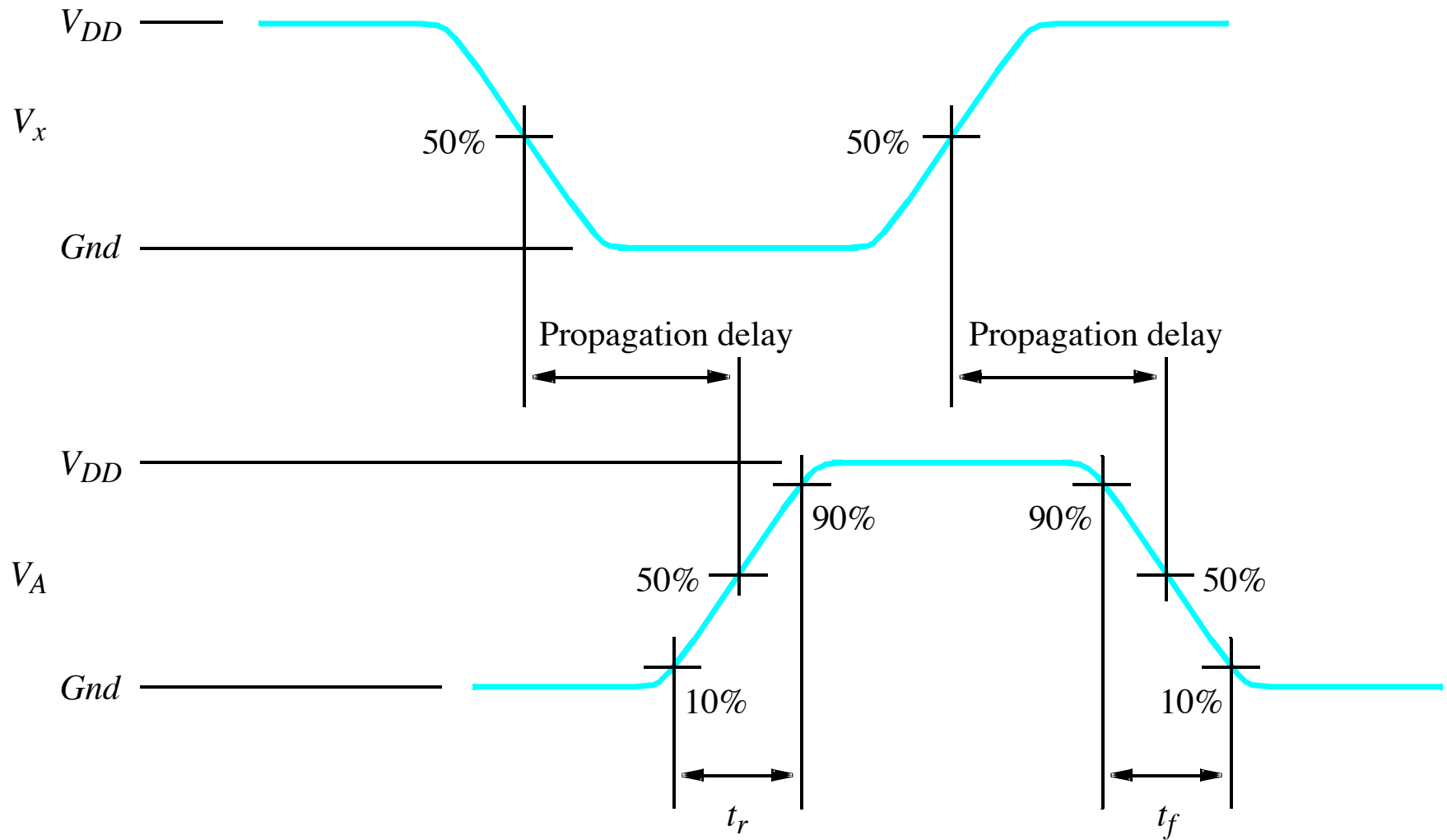
This capacitor takes time to charge and discharge (depends on the current  $I_d$  and the value of the capacitance)



(a) A NOT gate driving another NOT gate



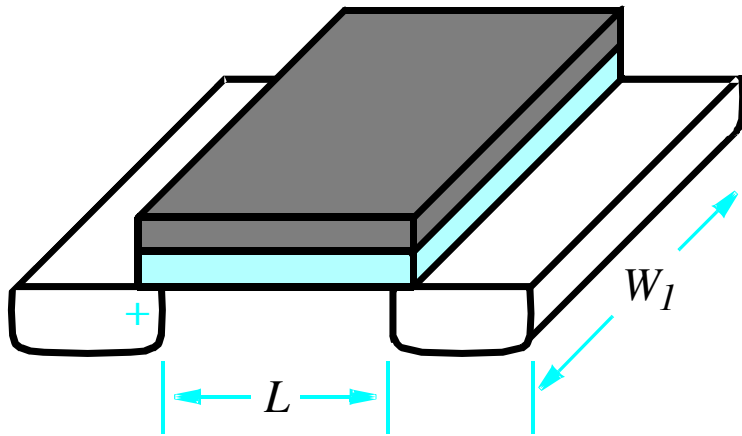
(b) The capacitive load at node A



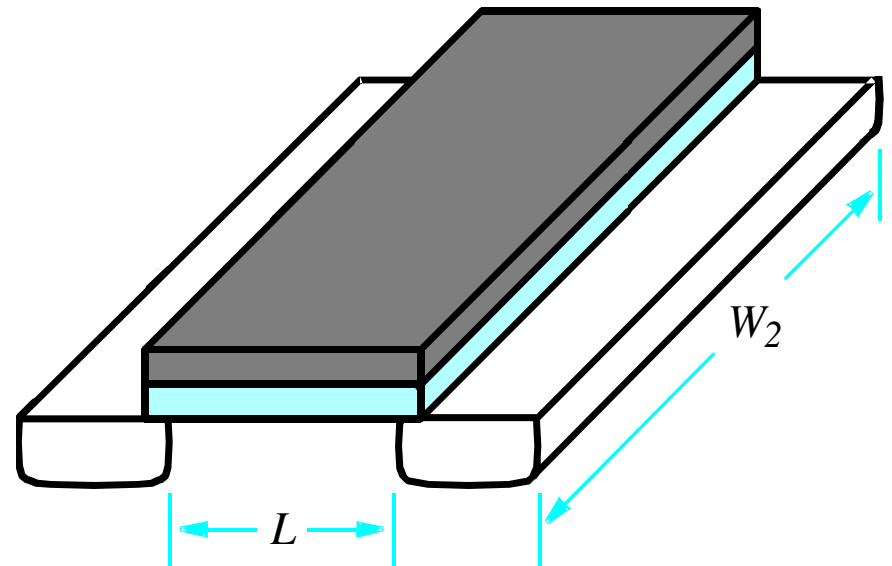
Voltage waveforms for logic gates



Size the PMOS and NMOS ( $W$  and  $L$ ) to make rise time and fall time roughly equal  
 $L$  is usually set to the minimum (e.g. 45 nm)



(a) Small transistor

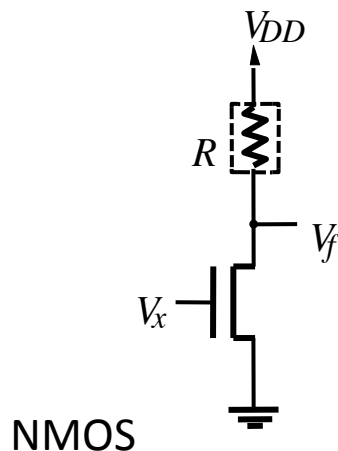


(b) Larger transistor

Transistor sizes

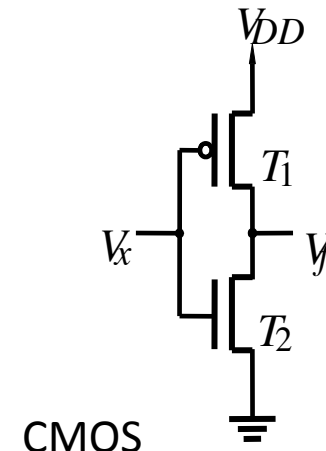
# Power Dissipation

- **Static power**: power due to current flow when the gate is in steady state
- **Dynamic power**: power due to current flow when the gate is switching (signals changing)
- **NMOS**: when  $V_x = 0V$ , no current flows  
when  $V_x = 5V$ , current flows  
→ static power consumption !!



- **CMOS**: No current flows in steady state for either  $V_x = 0V$  or  $V_x = 5V$
- --> zero static power consumption

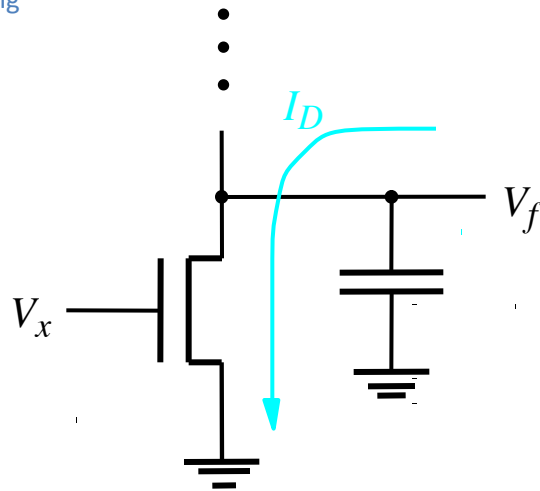
(in theory! in reality there is some static power because in modern technologies the transistor never fully turns off and also there are other mechanisms such as current leaking through the gate) – solving these problems are important to continue scaling CMOS



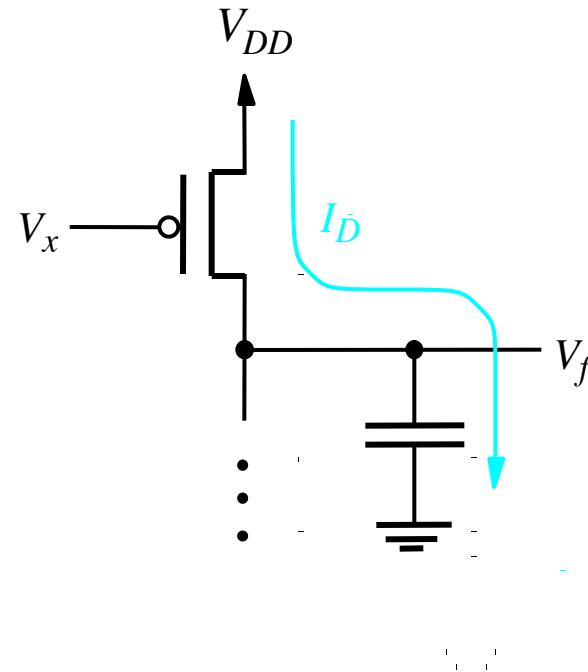
# Dynamic Power

Currents flow to charge and discharge the parasitic capacitor

There is also a small short-circuit current that flows for a short time when both transistors are on during switching



(a) Current flow when input  $V_x$  changes from 0 V to 5 V



(b) Current flow when input  $V_x$  changes from 5 V to 0 V

See Example 3.12 to find out why the energy stored in the capacitor is  $(1/2)CV_{DD}^2$  J

Every charge-discharge cycle dissipates  $CV_{DD}^2$  J

$$P_D = fCV_{DD}^2$$

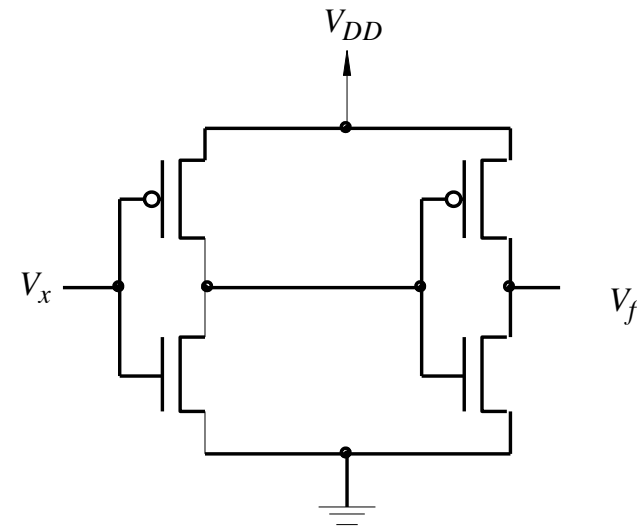
# Example

- If  $C = 70 \text{ fF}$  and  $f = 100 \text{ MHz}$ , the dynamic power consumed by a gate is  $175 \mu\text{W}$ .
- If the chip has the equivalent of 10,000 inverters and on average 20% of the gates change values at any given time then the total dynamic power used in the chip is

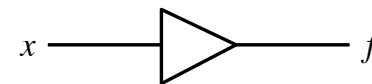
$$P_D = 0.2 \times 10,000 \times 175 \mu\text{W} = 0.35\text{W}$$

# Buffers

- When a logic gate has to drive a large capacitive load, it can be slow
- Use a buffer ( $f = x$ ) to improve performance
- Buffers usually are designed with large transistors to drive a large current
  - Used for driving long wires on the chip or for driving signals off the chip
- Often inserted by the CAD tools to meet performance goals



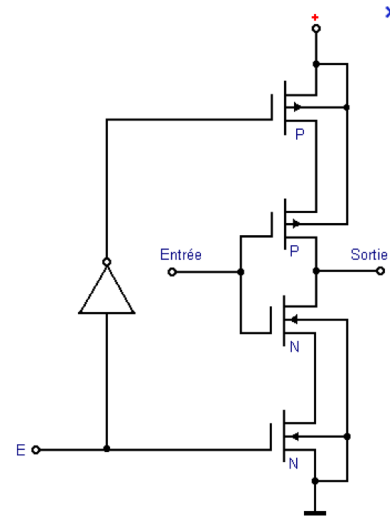
(a) Implementation of a buffer



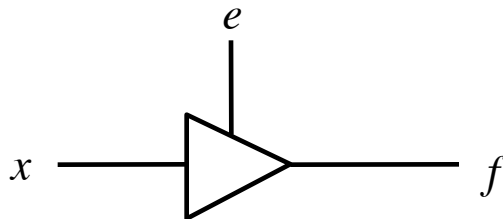
(b) Graphical symbol

# Tri-State Buffers

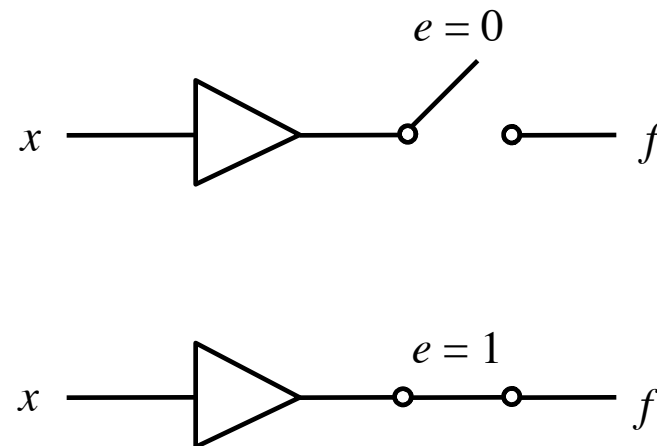
- When the control signal “enable” is low the buffer is completely disconnected from the output  $f$ 
  - When  $e$  is high, the buffers drives  $x$  onto  $f$
  - The disconnected state “Z” is “high impedance”



$e$	$x$	$f$
0	0	Z
0	1	Z
1	0	0
1	1	1



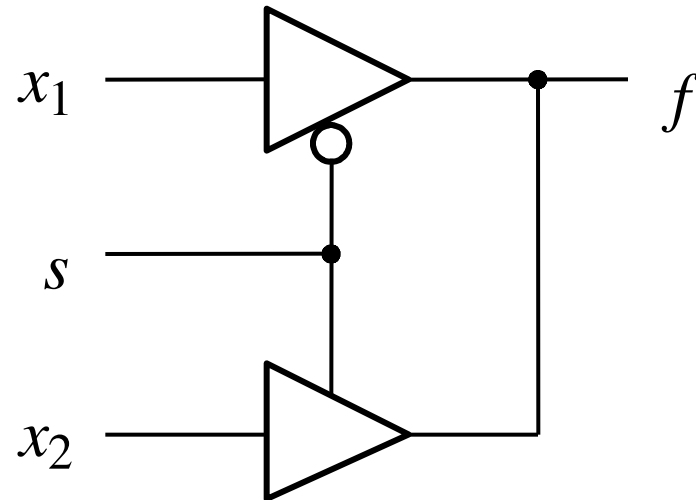
(a) A tri-state buffer



(b) Equivalent circuit

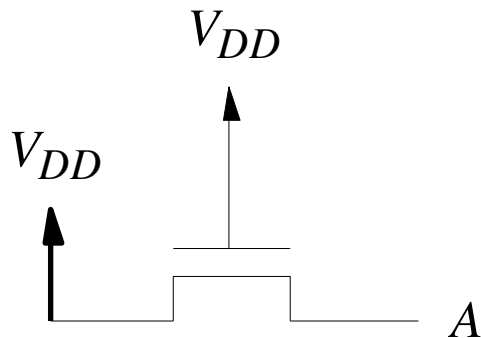
# Application of Tri-State Buffers

- Be careful! Connecting two gates (“drivers”) to the same line can short  $V_{DD}$  and Gnd! The CAD tools should warn you if this happens (although nothing stops you from doing this when connecting chips on a board).
- This is not the only way to choose signals (e.g. you can use multiplexers which we introduce in the next chapter)
  - Some technologies (e.g. FPGAs) may or may not have tri-states and if so, may only have them in certain places (e.g. output pins)
- Used in some cases, such as driving a common bus

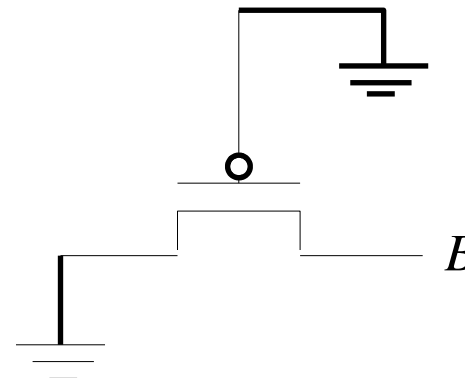


# Transmission Gates

- Why can't we use a single transistor as a switch and build logic out of that?
  - A single NMOS passes a '0', but doesn't fully pass a '1' (only pulls up to  $V_{DD} - V_t$ )
  - A single PMOS passes a '1', but doesn't fully pass a '0' (only pulls down to  $V_t$ )



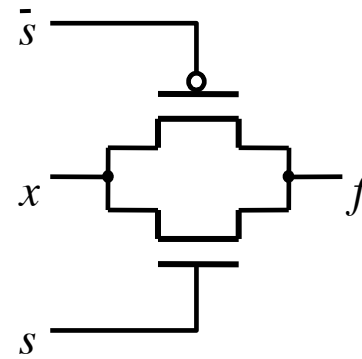
(a) NMOS transistor



(b) PMOS transistor



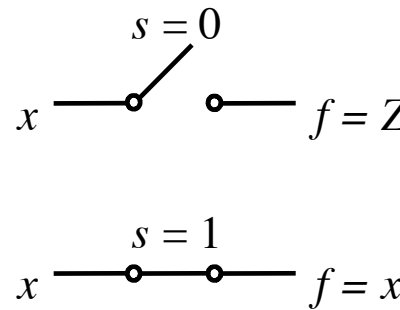
- The solution is to use both a NMOS and a PMOS to build the switch → **Transmission Gate**
- Only one (the appropriate) transistor is on for  $x = 0$  or  $x = 1$
- Can be used as alternative style for implementing logic circuits compared to “static CMOS” gates



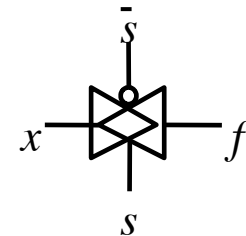
(a) Circuit

$s$	$f$
0	Z
1	$x$

(b) Truth table



(c) Equivalent circuit



(d) Graphical symbol